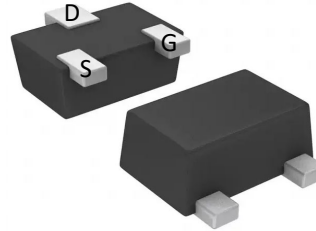


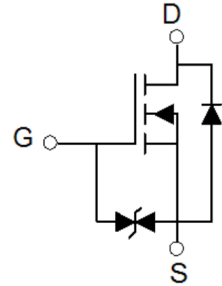
Features

- * $V_{DS} = 20V$, $I_D = 0.98A$
- * $R_{DS(ON)} = \text{Typ } 190m\Omega @ V_{GS} = 4.5V$
- * $R_{DS(ON)} = \text{Typ } 255m\Omega @ V_{GS} = 2.5V$
- * ESD protected
- * SOT-723 package

Package and Circuit Diagram

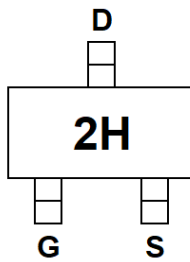


SOT-723



Circuit diagram

Marking diagram



Ordering Information

Part Number	Packaging	Reel Size
SSM3K35AMFV,L3F-CN	8000/Tape & Reel	7 inch

Absolute maximum ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current ($T_A = 25^\circ\text{C}$)	0.98	A
I_D	Continuous Drain Current ($T_A = 70^\circ\text{C}$)	0.6	A
I_{DM}	Pulsed Drain Current ^{note1}	3	A
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$)	0.2	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	625	$^\circ\text{C}/\text{W}$
T_J	Maximum Junction Temperature	$-40 \sim +150$	$^\circ\text{C}$
T_{STG}	Storage Temperature	$-55 \sim +150$	$^\circ\text{C}$

Electrical characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit	
Off characteristics							
V _{(BR)DS}	Drain-source breakdown voltage	V _{GS} = 0V, I _D = 250μA	20			V	
I _{DS}	Zero gate voltage drain current	V _{DS} = 16V, V _{GS} = 0V			1	μA	
I _{GS}	Gate to body leakage current	V _{DS} = 0V, V _{GS} = ±12V			± 10	μA	
On characteristics							
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250μA	0.5	0.75	1	V	
R _{DS(on)}	Static drain-source on resistance ^{Note2}	V _{GS} = 4.5V, I _D = 0.55A		190	230	mΩ	
		V _{GS} = 2.5V, I _D = 0.45A		255	330	mΩ	
		V _{GS} = 1.8V, I _D = 0.35A		365	550	mΩ	
Dynamic characteristics							
C _{iss}	Input capacitance	V _{DS} = 10V		41		pF	
C _{oss}	Output capacitance		V _{GS} = 0V		17		pF
C _{rss}	Reverse transfer capacitance		f = 1MHz		10		pF
Q _g	Total gate charge	V _{DS} = 10V		1		nC	
Q _{gs}	Gate-source charge		I _D = 1A		0.3		nC
Q _{gd}	Gate-drain charge		V _{GS} = 4.5V		0.1		nC
Switching characteristics							
td(on)	Turn-on delay time	V _{DS} = 10V		1.2		ns	
tr	Turn-on rise time		I _D = 1A		24.7		ns
td(off)	Turn-off delay time		R _{GEN} = 6Ω		13.6		ns
tf	Turn-off fall time		V _{GS} = 4.5V		14.8		ns
Drain-source diode characteristics and maximum ratings							
V _{SD}	Drain to source diode forward voltage	V _{GS} = 0V, I _S = 1A		0.85	1.1	V	
I _S	Maximum continuous drain to source diode forward current				0.98	A	
trr	Body diode reverse recovery time	I _F = 1A, di/dt = 100A/μs		9.2		ns	
Qrr	Body diode reverse recovery charge			0.8		nC	

Notes:1. Repetitive rating: pulse width limited by maximum junction temperature

2. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

Typical performance characteristics ($T_A=25^{\circ}\text{C}$ unless otherwiseSpecified)

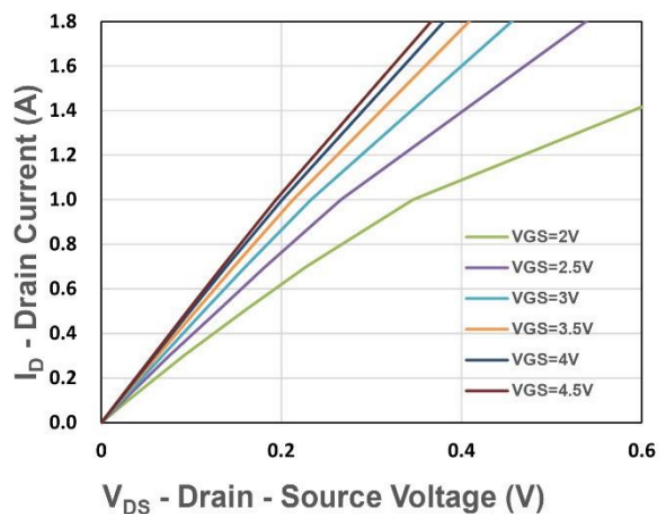


Figure 1. Output Characteristics

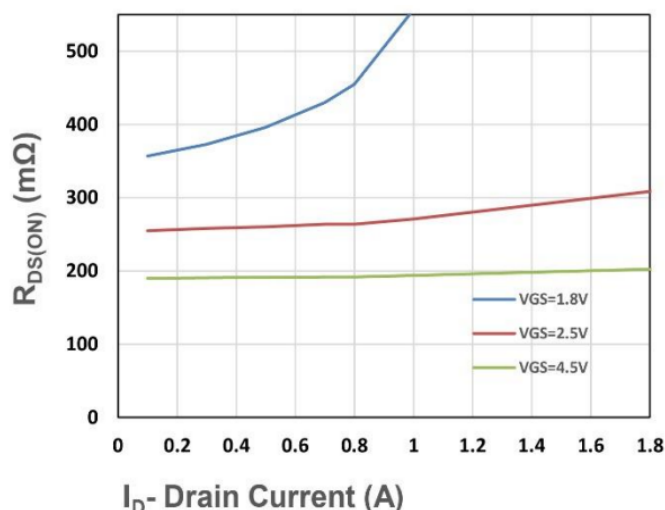


Figure 2. On-Resistance vs. ID

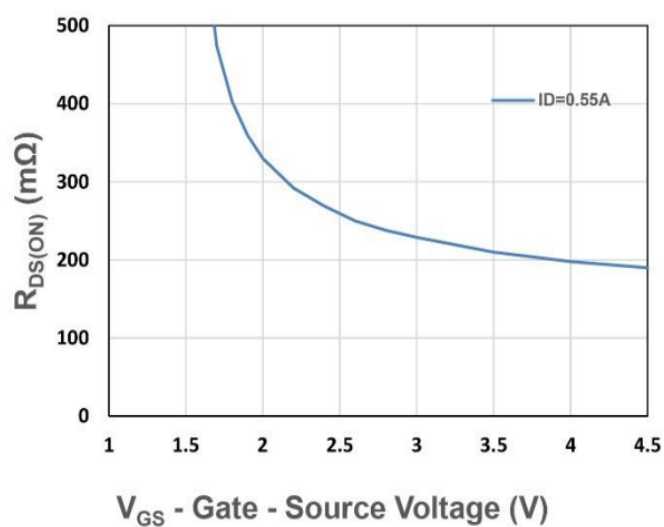


Figure 3. On-Resistance vs. VGS

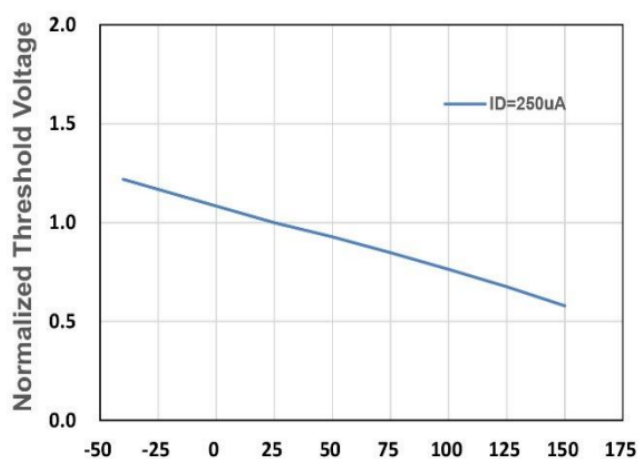


Figure 4. Gate Threshold Voltage

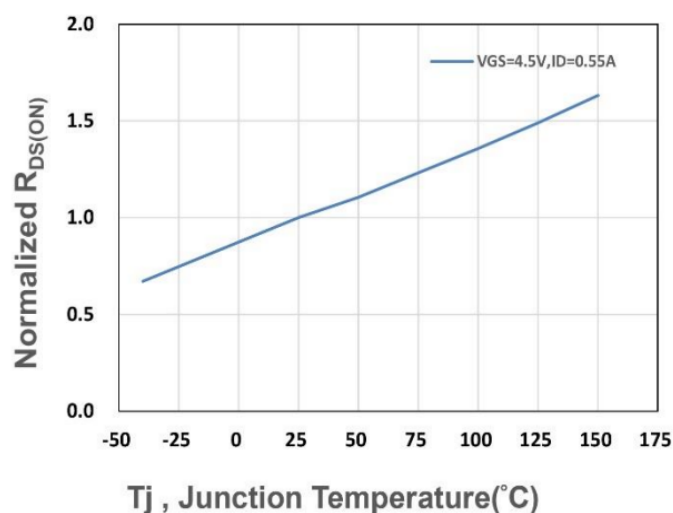


Figure 5. Drain-Source On Resistance

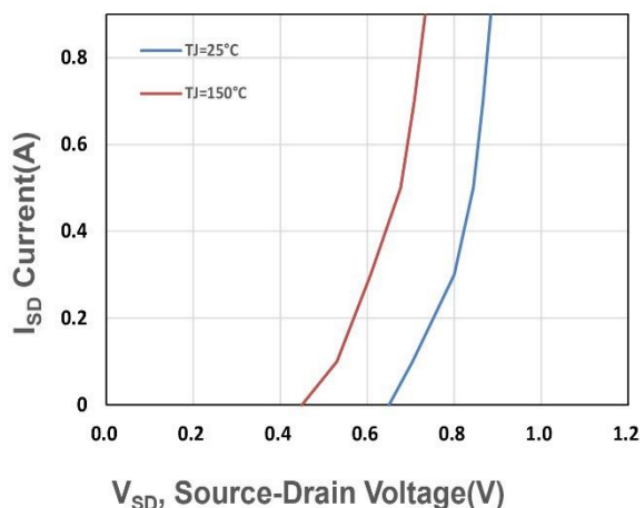
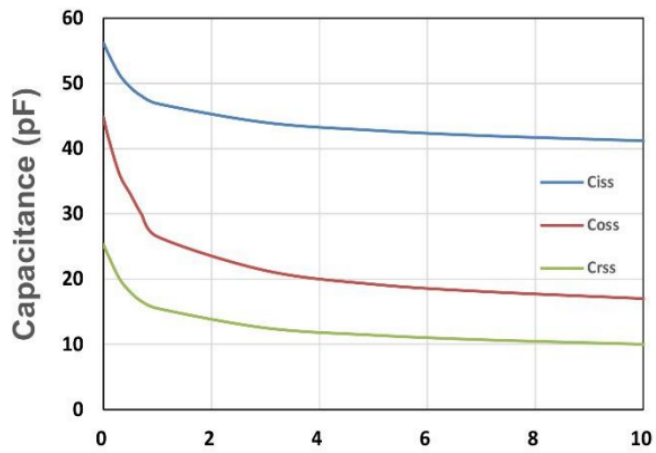
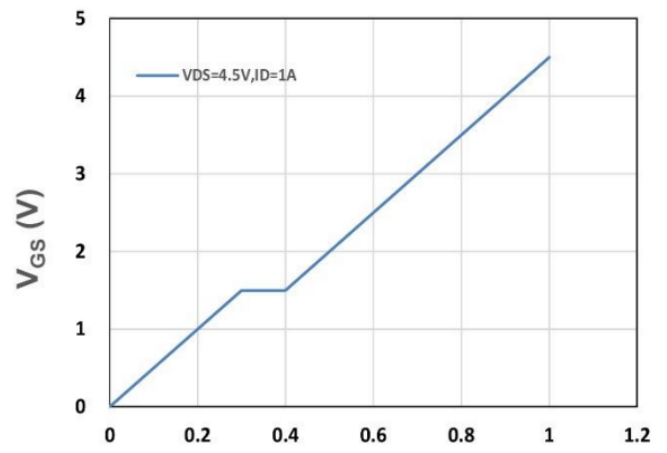


Figure 6. Source-Drain Diode Forward

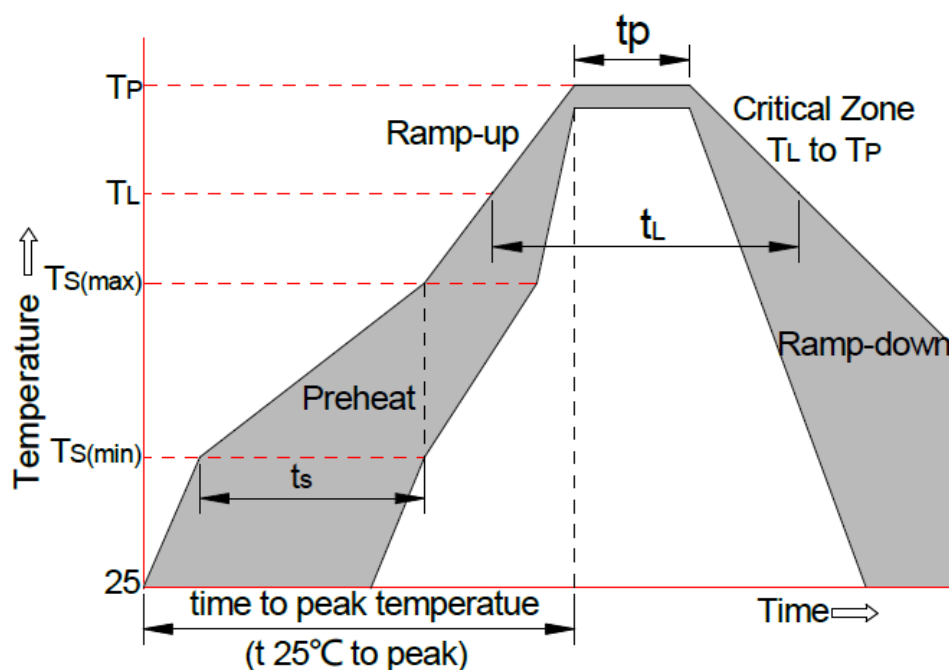


V_{DS} - Drain - Source Voltage (V)
Figure 7. Capacitance



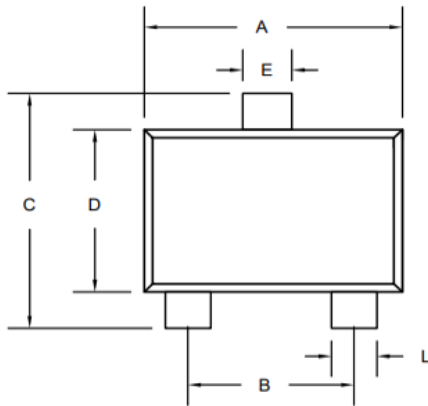
Q_g , Total Gate Charge (nC)
Figure 8. Gate Charge Characteristics

Soldering Parameters



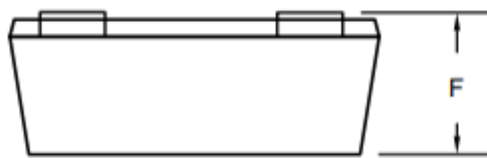
Reflow Conditions		Pb-Free Assembly
Pre-heat	-Temperature Min (T_S (min))	+150°C
	-Temperature Max (T_S (max))	+200°C
	-Time (Min to Max) (t_s)	60-180 secs
Average ramp up rate(Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{S(max)}$ to T_L -Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature (T_L) (Liquid us)	+217°C
	-Temperature (t_L)	60-150 secs
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6 °C/secs. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C

SOT-723 Package Outline Drawing

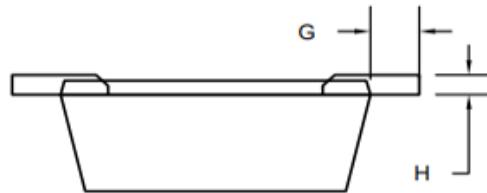


TOP VIEW

SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	Min	Typ	Max	Min	Typ	Max
A	1.10	1.20	1.30	0.0433	0.0472	0.0512
B	0.80 typ			0.0315 typ		
C	1.10	1.20	1.30	0.0433	0.0472	0.0512
D	0.70	0.80	0.90	0.0276	0.0315	0.0354
E	0.20	0.25	0.30	0.0079	0.0098	0.0118
F	0.40	0.45	0.50	0.0157	0.0177	0.0197
G	0.15	0.20	0.25	0.0059	0.0079	0.0098
H	0.06	0.11	0.16	0.0024	0.0043	0.0063
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

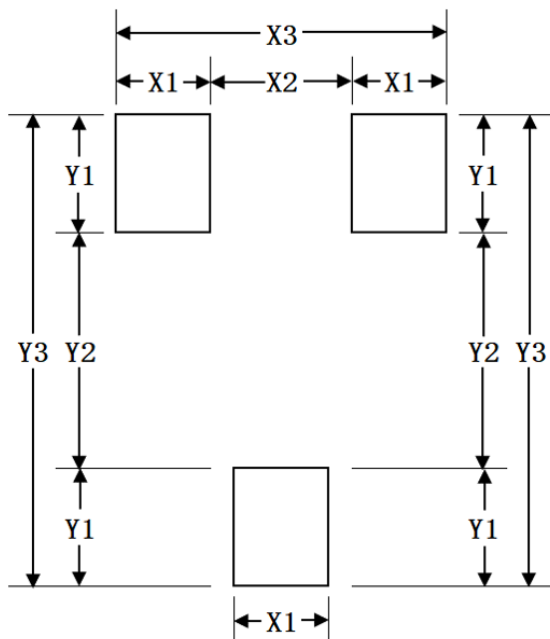


SIDE VIEW



SIDE VIEW

Suggested Pad Layout



SYM	DIMENSIONS	
	MILLIMETER	INCHES
X1	0.40	0.016
X2	0.55	0.022
X3	1.10	0.043
Y1	0.50	0.020
Y2	0.60	0.024
Y3	1.60	0.063

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